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ESREF2019 CONFERENCE PROGRAM

Monday, September 23

Tutorial 1

Room Guillaumet 1

08:50 *The Future of Reliability Testing*
J. Mcpherson
McPherson Reliability Consulting LLC

Tutorial 3

Room Guillaumet 2

08:50 *Introducing layered dielectrics in solid-state microelectronic devices*
M. Lanza
Institute of Functional Nano & Soft Materials, Soochow University

10:30 Coffee Break

Tutorial 2

Room Guillaumet 1

10:50 *Reliability of Power Electronic Packaging*
O. Wittler, A. Middendorf
Fraunhofer IZM

Tutorial 4

Room Guillaumet 2

10:50 *Methodology of soft error expertise applied for the use of embedded electronic devices in natural radiation environments*
L. Artola
ONERA - The French Aerospace Lab

12:30 Lunch

Session C1		Progress in Failure Analysis: Defect Detection and Analysis Room Cassiopée
chairpersons		I. DE WOLF J. GOXE
08:30		Invited paper *A completely new scanning electron microscope (SEM)* R. Schröder Univ. Heidelberg
09:10	**C1-1 #193**	*Cold temperature power on reset use case* M. Van Veenhuizen, D. Looijmans, M. Vogels, M. Van Aalten, P. Van Der Cruijsen, P. Gibas, S. Ersoy NXP Semiconductors
09:30	**C1-2 #109**	*Convolutional neural network (CNNs) based image diagnosis for failure analysis of power devices* A. Watanabe, N. Hirose, H. Kim, I. Omura Kyushu Institute of Technology
09:50	**C1-3 #250**	*Using infrared thermal responses for PCBA production tests: Feasibility study* N. El Belghiti Alaoui[1], A. Cassou[2], P. Tounsi[2], A. Boyer[2], A. Viard[1] [1]ACTIA Automotive, [2]LAAS
10:10	**C1-4 #163**	*Quantitative fractography analysis of a chip crack in a Si power MOSFET* R. Schneider Infineon Technologies AG

Session F2-1		GaN devices reliability Room Guillaumet 1
chairpersons		F. MORANCHO L. THEOLIER
09:10	**F2-1-1 #185**	*Buffer breakdown in GaN-on-Si HEMTs: a comprehensive study based on a sequential growth experiment* M. Borga[1], M. Meneghini[1], D. Benazzi[1], E. Canato[1], R. Püsche[2], J. Derluyn[2], F. Medjdoub[3], I. Abid[3], G. Meneghesso[1], E. Zanoni[1] [1]Department of information engineering, Univerrsity of Padova, [2]EpiGaN, [3]CNRS
09:30	**F2-1-2 #167**	*Stability and degradation of isolation and surface in Ga2O3 devices* C. De Santi[1], A. Nardo[1], M. H. Wong[2], K. Goto[3], A. Kuramata[4], S. Yamakoshi[5], H. Murakami[3], Y. Kumagai[3], M. Higashiwaki[2], G. Meneghesso[1], E. Zanoni[1], M. Meneghini[1] [1]University of Padova, [2]National Institute of Information and Communications Technology, [3]Department of Applied Chemistry, Tokyo University of Agriculture and Technology, [4]Novel Crystal Technology, Inc., [5]Tamura Corporation
09:50	**F2-1-3 #177**	*Characterization of charge trapping mechanisms in GaN vertical Fin FETs under positive gate bias* M. Ruzzarin[1], C. De Santi[1], F. Chiocchetta[1], M. Sun[2], T. Palacios[2], E. Zanoni[1], G. Meneghesso[1], M. Meneghini[1] [1]University of Padova, [2]MIT
10:10	**F2-1-4 #111**	*Stress and Recovery Dynamics of Drain Current in GaN HD-GITs Submitted to DC Semi-ON Stress* V. Padovan[1], C. Koller[2], G. Pobegen[2], C. Ostermaier[3], D. Pogany[4]